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APPLICATION NO	. 1	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.		
10/618,874	10/618,874 07/14/2003		Mukul Saran	TI-30597.1	5871		
23494	7590	06/17/2004		EXAM	EXAMINER		
TEXAS II	NSTRUM	ENTS INCORPOR	HA, NAT	HA, NATHAN W			
P O BOX 6 DALLAS,				ART UNIT	PAPER NUMBER		
	•			2814			
				DATE MAILED: 06/17/200	4		

Please find below and/or attached an Office communication concerning this application or proceeding.

				<u> </u>				
		Application No.	Applicant(s)					
		10/618,874	SARAN, MUKUL					
Office Action Summary		Examiner	Art Unit					
		Nathan W. Ha	2814					
Period for	The MAILING DATE of this communication a Reply	ppears on the cover sheet	with the correspondence addi	ress				
THE MA - Extension after SI - If the pe - If NO pe - Failure t Any repl	RTENED STATUTORY PERIOD FOR REPAILING DATE OF THIS COMMUNICATION one of time may be available under the provisions of 37 CFR (6) MONTHS from the mailing date of this communication. riod for reply specified above is less than thirty (30) days, a repriod for reply is specified above, the maximum statutory perion or reply within the set or extended period for reply will, by statily received by the Office later than three months after the main patent term adjustment. See 37 CFR 1.704(b).	I. 1.136(a). In no event, however, may eply within the statutory minimum of d will apply and will expire SIX (6) N ute, cause the application to become	y a reply be timely filed thirty (30) days will be considered timely. MONTHS from the mailing date of this come ABANDONED (35 U.S.C. § 133).	nmunication.				
Status								
1)⊠ R	esponsive to communication(s) filed on 4/1	/04.						
•		nis action is non-final.						
3)□ S	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is							
cl	closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.							
Disposition	n of Claims							
4)⊠ C	laim(s) 9-14 is/are pending in the application	on.						
4a	4a) Of the above claim(s) is/are withdrawn from consideration.							
5)□ C	Claim(s) is/are allowed.							
6)⊠ C	Claim(s) <u>9-14</u> is/are rejected.							
7) 🗌 C	Claim(s) is/are objected to.							
8)□ C	Claim(s) are subject to restriction and/or election requirement.							
Application	n Papers							
9)∐ Th	ne specification is objected to by the Exami	ner.						
10)□ Th)☐ The drawing(s) filed on is/are: a)☐ accepted or b)☐ objected to by the Examiner.							
Α	Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).							
R	Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).							
11)□ Th	ne oath or declaration is objected to by the	Examiner. Note the attach	ned Office Action or form PTC	D-152.				
Priority un	der 35 U.S.C. § 119	,						
a) <u>□</u> 1 2 3	cknowledgment is made of a claim for foreign All b) Some * c) None of: Certified copies of the priority docume. Copies of the certified copies of the priority docume copies of the priority docume the copies of the priority docume ce the attached detailed Office action for a lie	nts have been received. nts have been received ir iority documents have be eau (PCT Rule 17.2(a)).	n Application No en received in this National S	itage				
Attachment(s		_						
	of References Cited (PTO-892) of Draftsperson's Patent Drawing Review (PTO-948)		ew Summary (PTO-413) No(s)/Mail Date					
3) Informa	or Dransperson's Patent Drawing Review (P10-945) tion Disclosure Statement(s) (PTO-1449 or PTO/SB/0 lo(s)/Mail Date		of Informal Patent Application (PTO-	152)				

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DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

2. Claims 9-13 are rejected under 35 U.S.C. 102(e) as being anticipated by Ning et al. (US 6,677,635, newly cited, hereinafter, Ning.)

In regard to claim 9, in fig.5, Ning discloses a method of forming an IC capacitor, comprising:

providing a silicon substrate, not shown, with a first dielectric film 11 containing at least one copper layer 10, see also, col. 4, lines 7-10;

forming a second dielectric layer 12 over the first dielectric layer and the copper layer wherein the second dielectric layer contacts the copper layer;

forming a first conductive layer 16 over the first dielectric layer wherein the first conductive layer contacts the electric layer, see fig.5; and

removing portion of the first conductive layer such that a portion of the second dielectric layer remains between the first conductive layer and the copper layer wherein these layers formed a capacitor structure. See col. 4, lines 1-10.

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In regard to claim 10, Ning further discloses forming copper contacts to the first conductive layer, see fig.5; and

forming a second copper layer that electrically contacts the copper contacts.

In regard to claim 11, the first conductive layer suggested to be aluminum, see col. 4, lines 45-47.

In regard to claim 12, see fig.5, where the dielectric layer is formed using a least two dielectric films, including 15, for example.

In regard to claim 13, layer 12 may be considered as a barrier layer.

In regard to claim 14, the dielectric layer is made of silicon nitride. See col. 4, lines 15-17.

Response to Arguments

3. Applicant's arguments with respect to claims 9-14 have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

4. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not

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mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Nathan W. Ha whose telephone number is (571) 272-1707. The examiner can normally be reached on M-TH 8:00-7:00(EST).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on (571) 272-1705. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Nathan Ha June 12, 2004 Wael Fahrung SPE 2814